

Substitute for form 1449A/PTO				Complete If Known	
				Application Number	10/624,384
				Filing Date	July 22, 2003
				First Named Inventor	Leybovich
				Art Unit	1753
				Examiner Name	VerSteeg
Sheet	1	of	3	Attorney Docket Number	020324 227P2

U.S. PATENT DOCUMENTS						Class	Subclass
Examiner Initials*	Cite No. ¹	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns Where Relevant Passages or Relevant Figures Appear	Lines, Where Relevant Passages or Relevant Figures Appear	
SHV	AA	US-6,395,649	05-28-2002	Wu, Hui-Jung	438	778	
SHV	AB	US-6,340,435	01-22-2002	Bjorkman et al.	216	72	
	AC	US-					
	AD	US-					
	AE	US-					
	AF	US-					
	AG	US-					
	AH	US-					
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FOREIGN PATENT DOCUMENTS						
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Examiner Signature		Date Considered	March 17, 2005
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
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SHV	AK	CHAPMAN, B.; DC Glow Discharges, pp. 98-101	
SHV	AL	THOMAS, MICHAEL E.; Spin-On Stacked Films for Low-k _{eff} Dielectrics, Solid State Technology, July 2001, pp. 105-113	
SHV	AM	MAISSEL, Leon and GLANG, Reinhard; Handbook of Thin Film Technology, pp. 3-14—30-15, 3-24—3-27, 4-26—4-37, McGraw Hill Book Company	
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SHV	AR	SHIMOKAWA, F. and NAGAI, K.; A Low-Energy Fast-Atom Source, Nuclear Instruments and Methods in Physics Research B33 (1988) pp. 867-870	
SHV	AS	SHIMOKAWA, F., KUWANO, H. and NAGAI, K.; Energy Distribution of Fast Atom Beam Produced by an Fab Source, Proc. 10 th Symp. On ISIAT '86, Tokyo (1986) pp. 101-104	
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

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SHV	AU	GORBATOV, Y., VYATKIN, A. and ZINENKO, V.; A Low-Energy Fast-Atom Beam Source, Nuclear Instruments and Methods in Physics Research B55 (1991) 328-330	
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SHV	AY	MOUNTSIER et al.; Integration Studies of Plasma Deposited Fluorinated Amorphous Carbon, Low-Dielectric Constant Materials IV Symposium, pp. 259-64 1998 (Abstract)	
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